

**In the Claims:**

Please cancel claims 1-32 and 34-47 without prejudice:

Claims 1-32 (canceled).

33. (original) A semiconductor device comprising:

a semiconductor substrate;

a transistor formed on said semiconductor substrate;

an insulating film covering said semiconductor substrate and said transistor;

a contact plug buried in said insulating film and connected to a diffusion layer of said transistor; and

a ferroelectric capacitor formed on said insulating film and connected to said transistor by said contact plug,

said ferroelectric capacitor having a lower electrode, a ferroelectric film formed on said lower electrode, an upper electrode formed on and having an area smaller than said ferroelectric film, and a protective film formed in said alignment with side walls of said upper electrode to cover the surface of said ferroelectric film.

Claims 34-47 (canceled).

Serial No. TBA

Atty. Dkt. No. 002372.00043

**In the Title:**

Please change the title of the invention to:

SEMICONDUCTOR DEVICE HAVING FERROELECTRIC CAPACITOR AND  
HYDROGEN BARRIER FILM AND MANUFACTURING METHOD THEREOF